

NPN Transistors

2SC3650

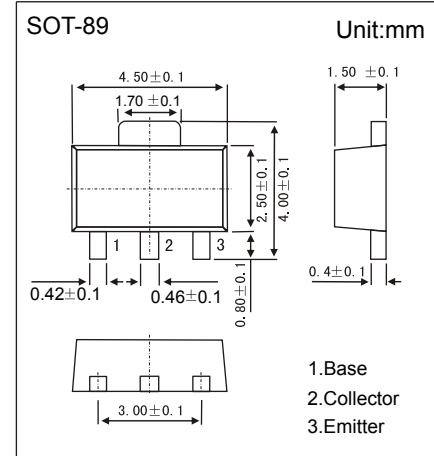
■ Features

- Collector Current Capability $I_c=1.2A$
- Collector Emitter Voltage $V_{CE0}=25V$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	30	V
Collector - Emitter Voltage	V_{CEO}	25	
Emitter - Base Voltage	V_{EBO}	15	
Collector Current - Continuous	I_c	1.2	A
Collector Current - Pulse	I_{CP}	2	
Collector Power Dissipation (Note.1)	P_c	0.5	W
		1.5	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1 : Mounted on ceramic substrate of 250mm²X0.8mm



■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = 100 \mu A, I_E = 0$	30			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = 1 mA, I_B = 0$	25			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu A, I_c = 0$	15			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 25 V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 10 V, I_c = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 500 mA, I_B = 10 mA$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 500 mA, I_B = 10 mA$			1.2	
DC current gain	h_{FE}	$V_{CE} = 5 V, I_c = 500 mA$	800		3200	
		$V_{CE} = 5 V, I_c = 10 mA$	600			
Collector output capacitance	C_{ob}	$V_{CB} = 10 V, f = 1 MHz$		17		pF
Transition frequency	f_T	$V_{CE} = 10 V, I_c = 50 mA$		220		MHz

■ Marking

Marking	CF
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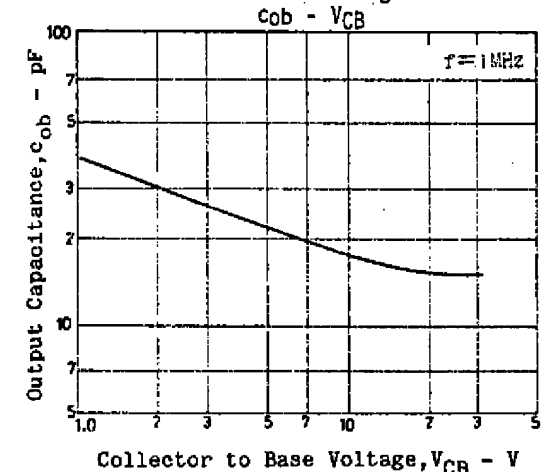
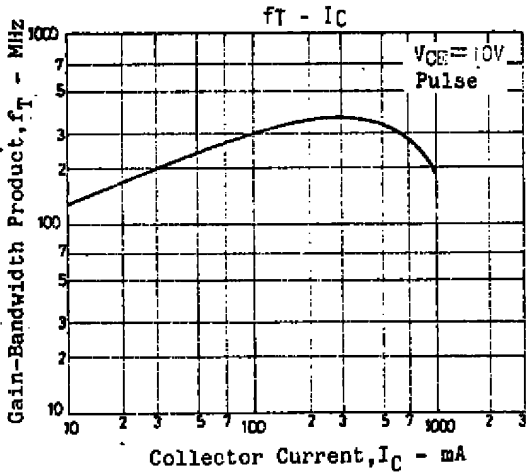
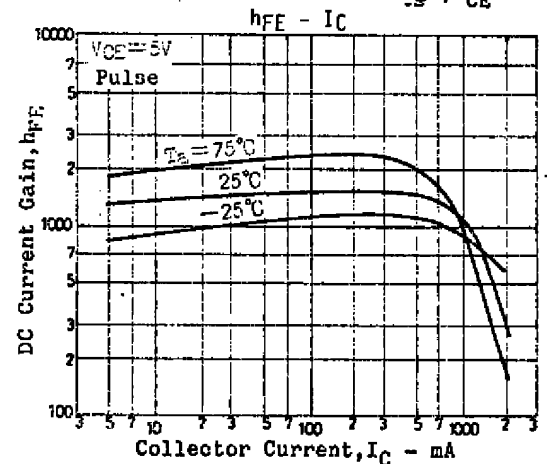
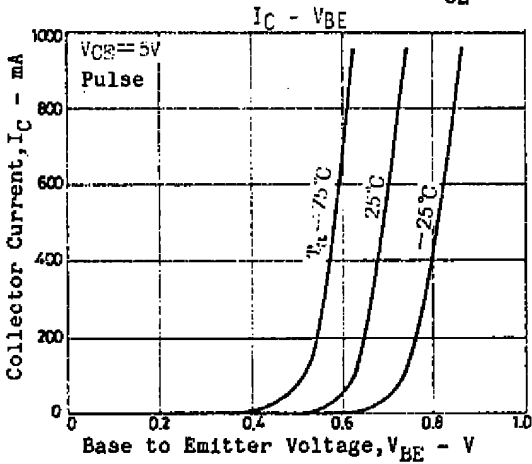
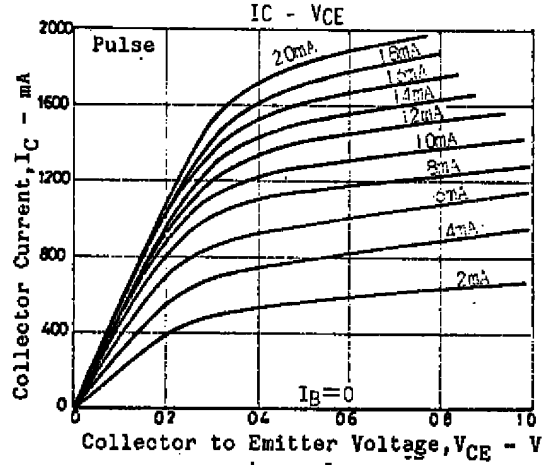
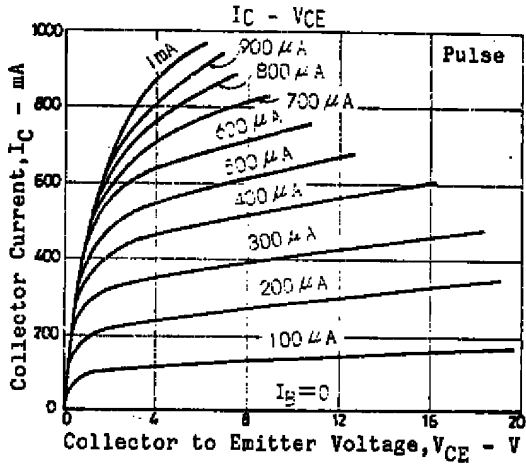


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Typical Characteristics





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